**Product data sheet** 

### 1. General description

PNP low V<sub>CEsat</sub> transistor in a medium power flat lead SOT89 plastic package.

NPN complement: PBSS4320X

### 2. Features and benefits

- SOT89 (SC-62) package
- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability: I<sub>C</sub> and I<sub>CM</sub>
- · Higher efficiency leading to less heat generation
- · Reduced printed-circuit board requirements.
- AEC-Q101 qualified

## 3. Applications

- Power management
  - · DC/DC converters
  - Supply line switching
  - Battery charger
  - · LCD backlighting.
- Peripheral drivers
  - Driver in low supply voltage applications (e.g. lamps and LEDs)
  - · Inductive load driver (e.g. relays, buzzers and motors).

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	-20	V
I <sub>C</sub>	collector current		[1]	-	-	-3	Α
I <sub>CM</sub>	peak collector current	limited by T <sub>j(max)</sub>		-	-	-5	Α
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = -2 V; I <sub>C</sub> = -0.1 A		220	-	-	
R <sub>CEsat</sub>	collector-emitter saturation resistance	I <sub>C</sub> = -3 A; I <sub>B</sub> = -300 mA	[2]	-	90	105	mΩ

<sup>[1]</sup> Device mounted on a ceramic printed-circuit board 7 cm<sup>2</sup>, single-sided copper, tin-plated.

[2] Pulsed test:  $t_p \le 300 \ \mu s$ ;  $\delta \le 0.02$ 



20 V, 3 A PNP low VCEsat (BISS) transistor

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter		C
2	С	collector		В—
3	В	base	3 2 1 SOT89	E sym132

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package		
	Name	Description	Version
PBSS5320X	SOT89	plastic surface-mounted package; die pad for good heat transfer; 3 leads	SOT89

# 7. Marking

### Table 4. Marking codes

Type number	Marking code
PBSS5320X	S45

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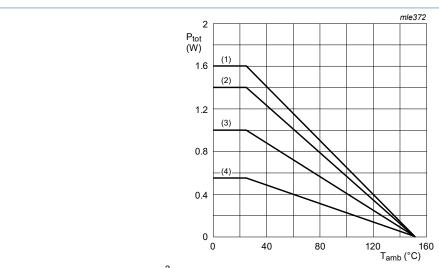
# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-20	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-20	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-5	V
I <sub>C</sub>	collector current		[1]	-	-3	Α
I <sub>CM</sub>	peak collector current	limited by T <sub>j(max)</sub>		-	-5	А
I <sub>B</sub>	base current			-	-0.5	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[2]	-	550	mW
			[3]	-	1	W
			[4]	-	1.4	W
			[1]	-	1.6	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- Device mounted on a ceramic printed-circuit board 7 cm<sup>2</sup>, single-sided copper, tin-plated.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup> [3]
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.



- (1) Ceramic PCB; 7 cm<sup>2</sup> mounting pad for collector (2) FR4 PCB; 6 cm<sup>2</sup> copper mounting pad for collector (3) FR4 PCB; 1 cm<sup>2</sup> copper mounting pad for collector
- (4) Standard footprint

**Power derating curves** Fig. 1.

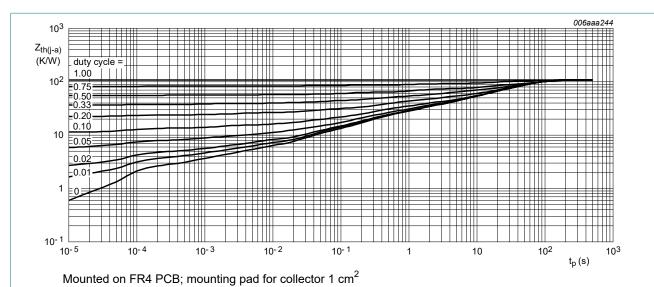
#### 20 V, 3 A PNP low VCEsat (BISS) transistor

### 9. Thermal characteristics

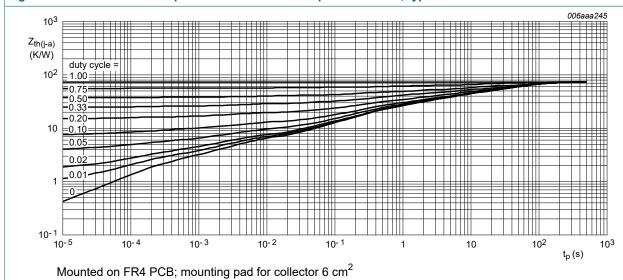
**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from	nt [2	[1]	-	-	225	K/W
	junction to ambient		[2]	-	-	125	K/W
			[3]	-	-	90	K/W
			[4]	-	-	80	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	16	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>. Device mounted on a ceramic printed-circuit board 7 cm<sup>2</sup>, single-sided copper, tin-plated.



Transient thermal impedance as a function of pulse duration; typical values Fig. 2.



Transient thermal impedance as a function of pulse duration; typical values

20 V, 3 A PNP low VCEsat (BISS) transistor

# 10. Characteristics

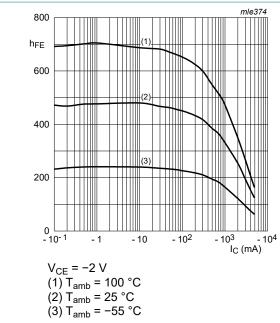
#### **Table 7. Characteristics**

 $T_{amb}$  = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = -20 V; I <sub>E</sub> = 0 A		-	-	-100	nA
	current	V <sub>CB</sub> = -20 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C		-	-	-50	μA
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = -20 V; V <sub>BE</sub> = 0 V		-	-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = -5 V; I <sub>C</sub> = 0 A		-	-	-100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = -2 V; I <sub>C</sub> = -0.1 A		220	-	-	
		V <sub>CE</sub> = -2 V; I <sub>C</sub> = -0.5 A		220	-	-	
		V <sub>CE</sub> = -2 V; I <sub>C</sub> = -1 A	[1]	200	-	-	
		V <sub>CE</sub> = -2 V; I <sub>C</sub> = -2 A	[1]	150	-	-	
		V <sub>CE</sub> = -2 V; I <sub>C</sub> = -3 A	[1]	100	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = -0.5 A; I <sub>B</sub> = -50 mA		-	-	-70	mV
		I <sub>C</sub> = -1 A; I <sub>B</sub> = -50 mA		-	-	-130	mV
		I <sub>C</sub> = -2 A; I <sub>B</sub> = -100 mA		-	-	-230	mV
		I <sub>C</sub> = -3 A; I <sub>B</sub> = -300 mA	[1]	-	-	-300	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance		[1]	-	90	105	mΩ
V <sub>BEsat</sub>	base-emitter saturation	I <sub>C</sub> = -2 A; I <sub>B</sub> = -100 mA		-	-	-1.1	V
	voltage	I <sub>C</sub> = -3 A; I <sub>B</sub> = -300 mA	[1]	-	-	-1.2	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE} = -2 \text{ V}; I_{C} = -1 \text{ A}$		-1.1	-	-	V
f <sub>T</sub>	transition frequency	V <sub>CE</sub> = -5 V; I <sub>C</sub> = -100 mA; f = 100 MHz		100	-	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB}$ = -10 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; $f$ = 1 MHz		-	-	50	pF

<sup>[1]</sup> Pulsed test:  $t_p \le 300 \ \mu s; \ \delta \le 0.02$ 

#### 20 V, 3 A PNP low VCEsat (BISS) transistor

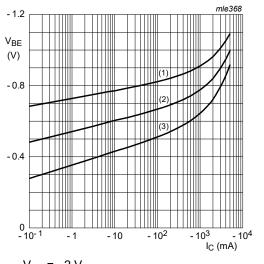


$$V_{CE} = -2 V$$

$$(1) I_{amb} = 100^{\circ} ($$

$$(3) T_{amb} = -55 °C$$

Fig. 4. DC current gain as a function of collector current; typical values



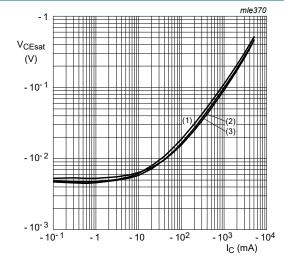
$$V_{CE} = -2 V$$

$$V_{CE} = -2 V$$
  
(1)  $T_{amb} = -55 °C$   
(2)  $T_{amb} = 25 °C$ 

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 5. Base-emitter voltage as a function of collector current; typical values



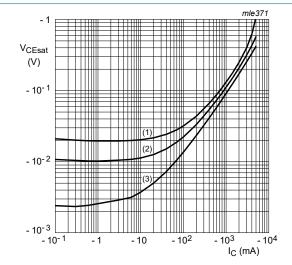
$$I_{\rm C}/I_{\rm B}=20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = -55 °C$$

Fig. 6. Collector-emitter saturation voltage as a function of collector current; typical values



(1) 
$$I_C/I_B = 100$$

(2) 
$$I_C/I_B = 50$$

(3) 
$$I_C/I_B = 10$$

Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values

### 20 V, 3 A PNP low VCEsat (BISS) transistor

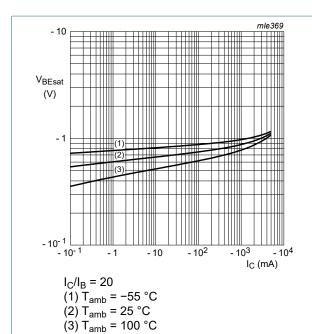
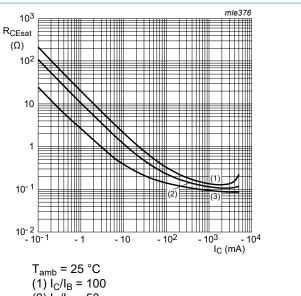
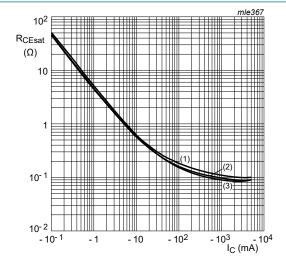


Fig. 8. Base-emitter saturation voltage as a function of Fig. 9. collector current; typical values



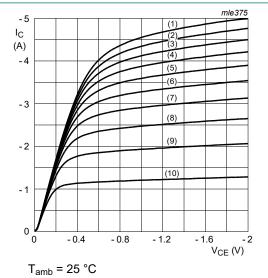
(2)  $I_C/I_B = 50$ (3)  $I_C/I_B = 10$ 

Equivalent on-resistance as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 20$ (1) T<sub>amb</sub> = 100 °C (2) T<sub>amb</sub> = 25 °C (3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig. 10. Equivalent on-resistance as a function of collector current; typical values



(1)  $I_B = -25 \text{ mA}$  $(2) I_B = -22.5 \text{ mA}$ (3)  $I_B = -20 \text{ mA}$  $(4) I_B = -17.5 \text{ mA}$  $(5) I_B = -15 \text{ mA}$ (6)  $I_B = -12.5 \text{ mA}$ (7)  $I_B = -10 \text{ mA}$ (8)  $I_B = -7.5 \text{ mA}$ (9)  $I_B = -5 \text{ mA}$  $(10)^{-1}I_B = -2.5 \text{ mA}$ 

Fig. 11. Collector current as a function of collectoremitter voltage; typical values

20 V, 3 A PNP low VCEsat (BISS) transistor

## 11. Test information

### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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# 12. Package outline

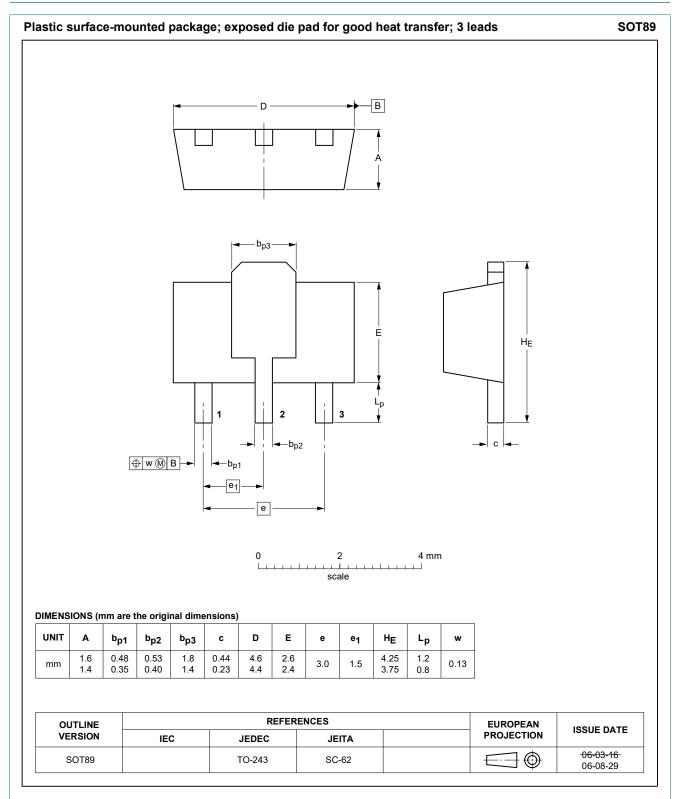
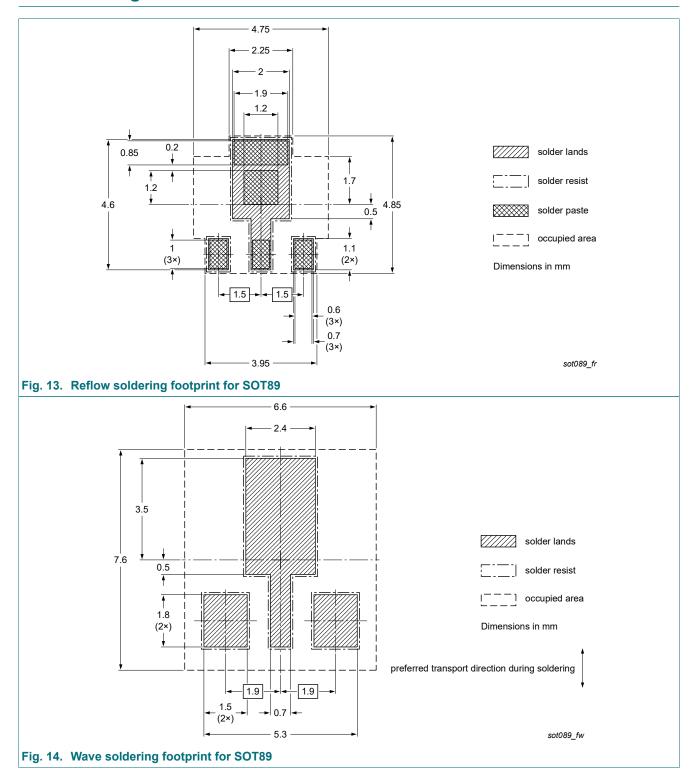


Fig. 12. Package outline SOT89

### 20 V, 3 A PNP low VCEsat (BISS) transistor

# 13. Soldering



## 20 V, 3 A PNP low VCEsat (BISS) transistor

# 14. Revision history

### **Table 8. Revision history**

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Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PBSS5320X v.3	20190527	Product data sheet	-	PBSS5320X v.2		
Modifications:	<ul> <li>Characteristics: V<sub>BEsat</sub> corrected from typical to maximum.</li> <li>The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia.</li> <li>Legal texts have been adapted to the new company name where appropriate.</li> </ul>					
PBSS5320X v.2	20041104	Product data sheet	-	PBSS5320X v.1		
PBSS5320X v.1	20031127	Product data sheet	-	-		

### 20 V, 3 A PNP low VCEsat (BISS) transistor

### 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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